D1MPM400

100V P-Channel MOSFETs

General Description

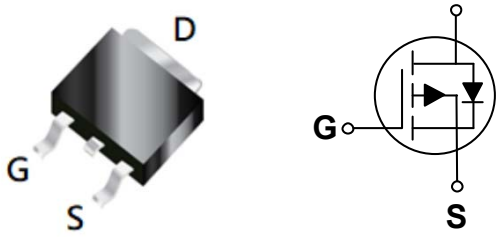
These P-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BV_{DSS}	$R_{DS(ON)}$	I_D
-100 V	400 mΩ	-10 A

Features

- $R_{DS(ON)} \leqq 400m\Omega @ V_{GS}$= -10V
- Fast Switching
- Green Device Available
- Improved dv/dt Capability

TO-252 Pin Configuration



Applications

- Auto Alarm Controller
- POS
- Brushless Motor

Absolute Maximum Ratings T_C=25°C unless otherwise noted

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	±20	V
I_D	Drain Current - Continuous (T_A=25°C)	-10	A
I_{DM}	Drain Current - Pulsed (NOTE 1)	-50	A
P_D	Power Dissipation (T_C=25°C)	19.3	W
T_J	Operating Junction Temperature Range	-55 to 150	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
Marking Code		PM400	

Thermal Characteristics

Symbol	Parameter	Rating	Unit
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	60	°C/W
$R_{\theta JC}$	Thermal Resistance Junction to Case	6.45	°C/W

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}= 0V , I_D= -250uA	-100	---	---	V
I_{DSS}	Drain-Source Leakage Current	V_{DS}= -100V , V_{GS}= 0V	---	---	-1	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}= ±20V , V_{DS}= 0V	---	---	±100	nA

On Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}= -10V , I_D= -3A	---	---	400	mΩ
		V_{GS}= -4.5V , I_D= -2A	---	---	420	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D= -250uA	-1.2	---	-2.5	V
gfs	Forward Transconductance	V_{DS}= -5V , I_D= -0.8A	---	3	---	S

Dynamic and switching Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
Q_g	Total Gate Charge	V_{DS}= -15V , V_{GS}= -4.5V , I_D= -0.5A	---	4.5	---	nC
Q_{gs}	Gate-Source Charge		---	1.14	---	
Q_{gd}	Gate-Drain Charge		---	1.5	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}= -50V , V_{GS}= -10V , R_G= 3.3Ω , I_D= -0.5A	---	17.6	---	ns
T_r	Rise Time		---	2.7	---	
$T_{d(off)}$	Turn-Off Delay Time		---	4.5	---	
T_f	Fall Time		---	3	---	
C_{iss}	Input Capacitance	V_{DS}= -15V , V_{GS}= 0V , F= 1MHz	---	550	---	pF
C_{oss}	Output Capacitance		---	56	---	
C_{rss}	Reverse Transfer Capacitance		---	35	---	
R_g	Gate resistance	V_{GS}= 0V , V_{DS}= 0V , F=1MHz	---	16	---	Ω

Drain-Source Diode Characteristics and Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	V_G= V_D= 0V , Force Current	---	---	-3	A
V_{SD}	Diode Forward Voltage	V_{GS}= 0V , I_S= -1A	---	---	-1.3	V

NOTES：

1. Repetitive Rating：Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%.
3. The data is theoretically the same as ID and I_{DM} , in real applications , should be limited by total power dissipation.

Characteristics Curves

FIG. 1-Power Dissipation

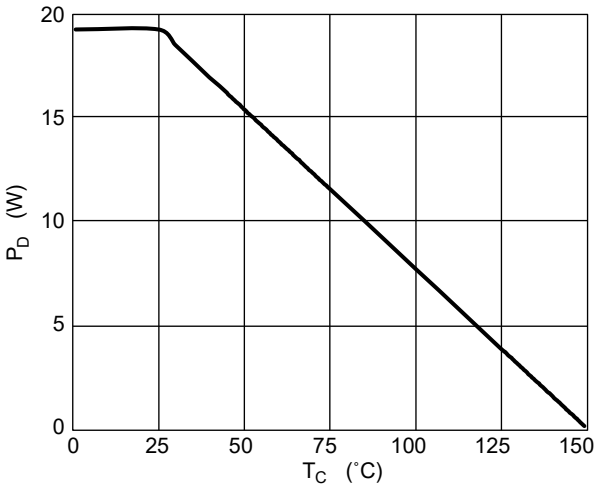


FIG. 2-$R_{DS(ON)}$ vs V_{GS}

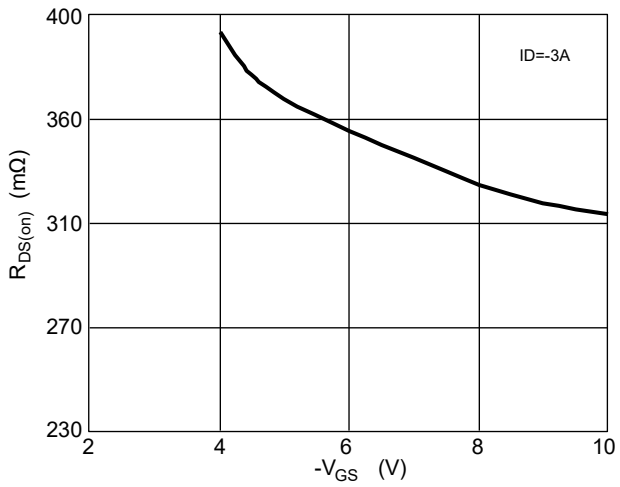


FIG. 3-I_S vs V_{SD}

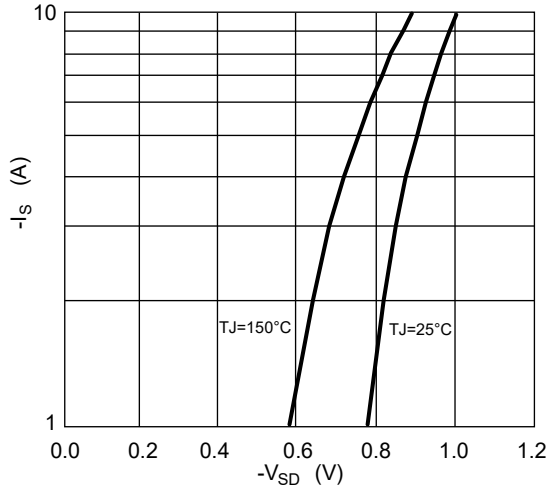


FIG. 4-Normalized $V_{GS(th)}$ vs T_J

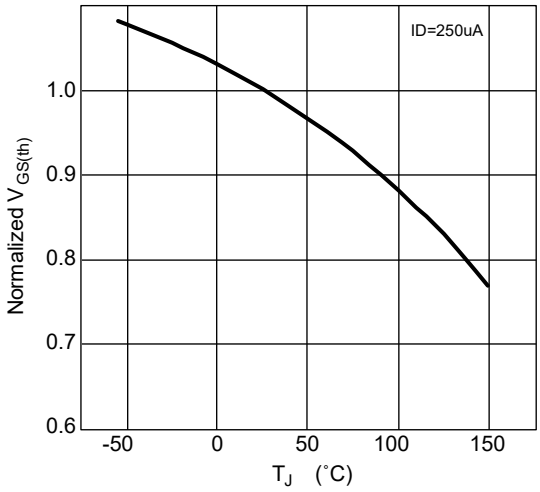


FIG. 5 - Switching Time Waveform

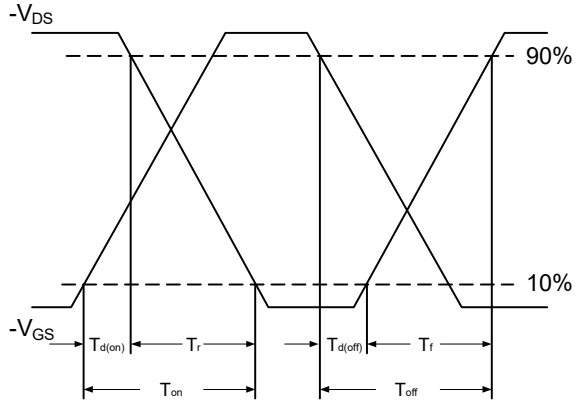
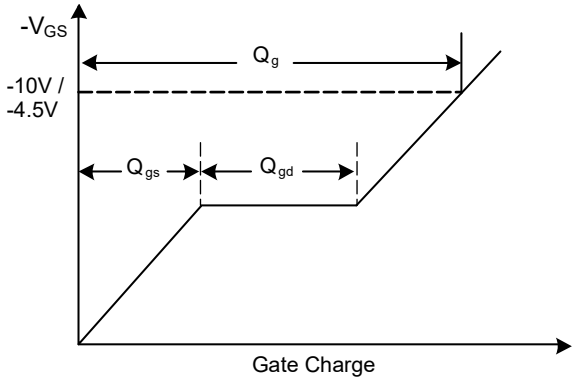
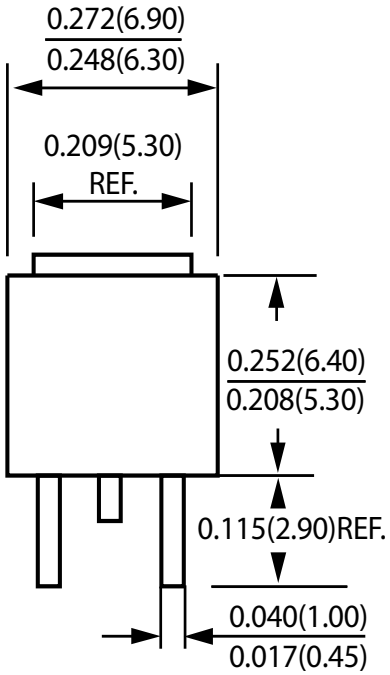
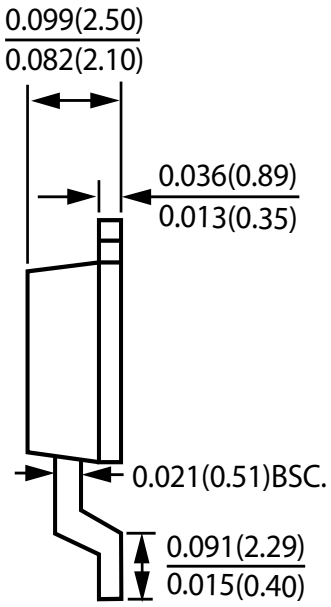


FIG. 6-Gate Charge Waveform



Package Outline Dimensions





TO-252

Dimensions in inches and (millimeters)

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